

Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended): A method of fabricating a semiconductor device comprising:

- forming a first layer on a semiconductor element;
- forming a second layer on said first layer, said second layer being made of a material having material[[,]] an etching rate [[of]] which changes in accordance with kind and concentration of dopant atoms implanted therein;
- implanting dopant atoms into said second layer;
- forming a third layer on said second layer;
- forming one or more first openings in said third layer;
- etching said second layer using said third layer as a first mask, thereby forming one or more second openings in said second layer; and
- forming one or more contact holes in said first layer using at least said second layer as a second mask,
- wherein a plurality of said first openings are formed in said third layer as having a same diameter, during said forming one or more first openings,
- a plurality of said second openings are formed in said second layer as having

different diameters, during said etching, and

a plurality of said contact holes are formed in said first layer including at least one large-diameter contact hole and at least one small-diameter contact hole, during said forming one or more contact holes.

Claim 2 (Currently Amended): The method according to claim 1, wherein said first mask used ~~[[in]]~~ during said forming ~~process~~ of one or more contact holes has a multilayer structure including said second layer and said third layer.

Claim 3 (Currently Amended): The method according to claim 1, further comprising:
annealing said second layer after said implanting ~~process~~ of dopant atoms,
thereby activating said dopant atoms.

Claim 4 (Canceled)

Claim 5 (Currently Amended): A method of fabricating a semiconductor device comprising:

forming a first layer on a semiconductor element;

forming a second layer on said first layer, said second layer being made of a material having an etching rate which changes in accordance with kind and concentration of dopant atoms implanted therein;

implanting dopant atoms into said second layer;
forming a third layer on said second layer;
forming one or more first openings in said third layer;
etching said second layer using said third layer as a first mask, thereby forming
one or more second openings in said second layer; and
forming one or more contact holes in said first layer using at least said second
layer as a second mask ~~The method according to claim 4,~~

wherein said implanting ~~process of~~ dopant atoms is performed ~~in such a way so~~
that said dopant atoms are implanted into said second layer inside a specific area and
are not implanted into said second layer outside said specific area[[;]], and

said forming ~~process of~~ one or more first openings is performed ~~in such a way so~~
that at least one of said first openings is formed in said third layer inside said specific
area and ~~the rest others~~ of said first openings [[is]] are formed in said third layer outside
said specific area.

Claim 6 (Currently Amended): A method of fabricating a semiconductor device
comprising:

forming a first layer on a semiconductor element;
forming a second layer on said first layer, said second layer being made of a
material having an etching rate which changes in accordance with kind and
concentration of dopant atoms implanted therein;

implanting dopant atoms into said second layer;
forming a third layer on said second layer;
forming one or more first openings in said third layer;
etching said second layer using said third layer as a first mask, thereby forming
one or more second openings in said second layer; and
forming one or more contact holes in said first layer using at least said second
layer as a second mask ~~The method according to claim 4,~~

wherein said implanting ~~process of~~ dopant atoms is performed ~~in such a way so~~ that said dopant atoms include first dopant atoms and second dopant atoms different from said first dopant atoms, said first dopant atoms are implanted into said second layer inside ~~[[said]]~~ a specific area, and said second dopant atoms are implanted into said second layer outside said specific area~~[[;]]~~, and

said forming ~~process of~~ one or more first openings is performed ~~in such a way so~~ that at least one of said first openings is formed in said third layer inside said specific area and ~~the rest~~ others of said first openings ~~[[is]]~~ are formed in said third layer outside said specific area.

Claim 7 (Currently Amended): The method according to claim 1 ~~[[4]]~~, wherein said implanting ~~process of~~ dopant atoms is performed ~~in such a way so~~ that said dopant atoms are implanted into a whole area of said second layer.

Claim 8 (Original): The method according to claim 1, wherein said first layer is an interlayer insulating film.

Claim 9 (Original): The method according to claim 1, wherein said second layer is a polysilicon layer.

Claim 10 (Currently Amended): The method according to claim 1, wherein said second layer is ~~formed of~~ a dielectric material.

Claim 11 (Original): The method according to claim 1, wherein said third layer is a resist layer.

Claim 12 (Currently Amended): The method according to claim 1, wherein said forming ~~process of~~ one or more first openings in said third layer is performed using photolithography.

Claim 13 (Original): The method according to claim 1, wherein said dopant atoms are either group V atoms or group III atoms.

Claim 14 (Original): The method according to claim 6, wherein said first dopant atoms are group V atoms and said second dopant atoms are group III atoms.

Claim 15 (Currently Amended): The method according to claim 1 [[4]], wherein[[[:]] said semiconductor element has a gate, a source and a drain;

said at least one large-diameter contact hole is formed directly above said gate;

and

said at least one small-diameter contact hole is ~~holes are~~ formed directly above at least one of said source and said drain.

Claim 16 (New): The method according to claim 6, wherein said first mask used during said forming one or more contact holes has a multilayer structure including said second layer and said third layer.

Claim 17 (New): The method according to claim 6, further comprising:

annealing said second layer after said implanting dopant atoms, thereby activating said dopant atoms.

Claim 18 (New): The method according to claim 6, wherein said first layer is an interlayer insulating film.

Claim 19 (New): The method according to claim 6, wherein said second layer is a polysilicon layer.

Claim 20 (New): The method according to claim 6, wherein said second layer is a dielectric material.

Claim 21 (New): The method according to claim 6, wherein said third layer is a resist layer.

Claim 22 (New): The method according to claim 6, wherein said forming one or more first openings in said third layer is performed using photolithography.

Claim 23 (New): The method according to claim 6, wherein said dopant atoms are either group V atoms or group III atoms.